

**FOR LOW FREQUENCY AMPLIFY APPLICATION
N CHANNEL JUNCTION TYPE**

DESCRIPTION

2SK433 is a super mini outline resin sealed silicon N channel junction type FET. It is designed for low frequency voltage amplify,application, analog switch application.

FEATURE

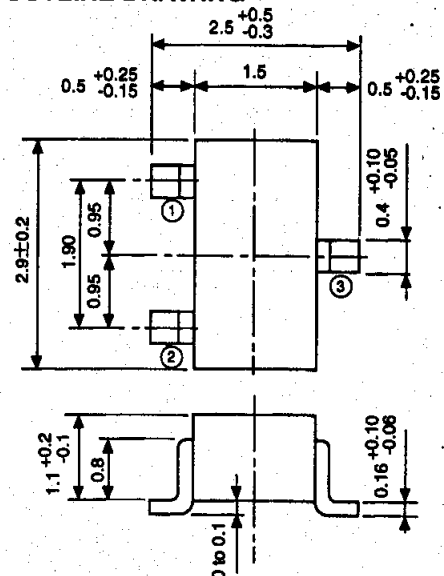
- Small type for mounting
- High $|y_{fs}|$ $|y_{fs}|=4\text{mS}(\text{typ})$
- Low $R_{DS(ON)}$ $R_{DS(ON)}=250\Omega$ typ

APPLICATION

General purpose voltage amplify,analog switch circuit for stereo,cassette deck,VCR.

OUTLINE DRAWING

Unit:mm



TERMINAL CONNECTOR

- ① : SOURCE
- ② : DRAIN
- ③ : GATE

EIAJ : SC-59

JEDEC : TO-236 resemblance

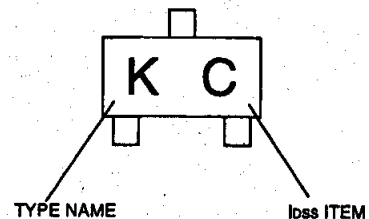
Note)

The dimension without tolerance represent central value.

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

Symbol	Parameter	Ratings	Unit
V_{GDO}	Gate to Drain voltage	-50	V
I_G	Gate current	10	mA
P_T	Total allowable dissipation($T_a=25^\circ\text{C}$)	150	mW
T_{ch}	Channel temperature	+125	$^\circ\text{C}$
T_{stg}	Storage temperature	-55 to +125	$^\circ\text{C}$

MARKING



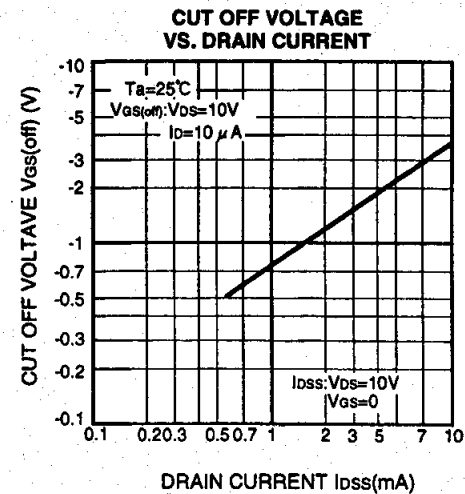
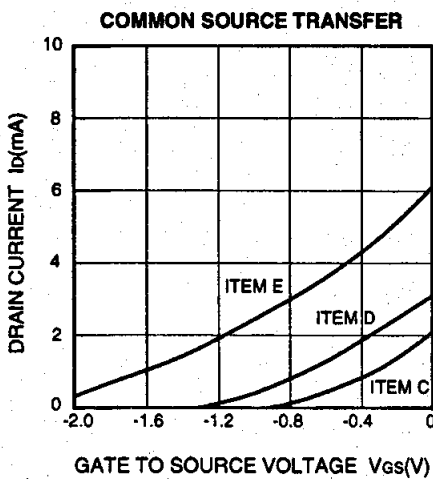
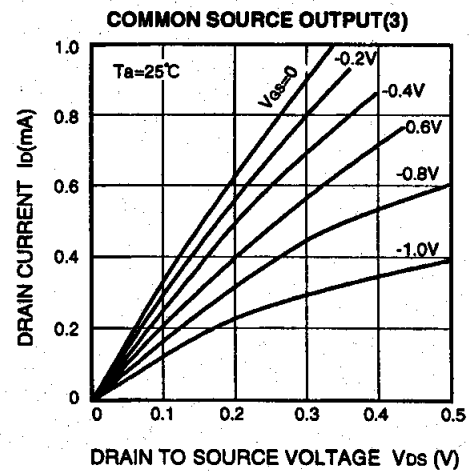
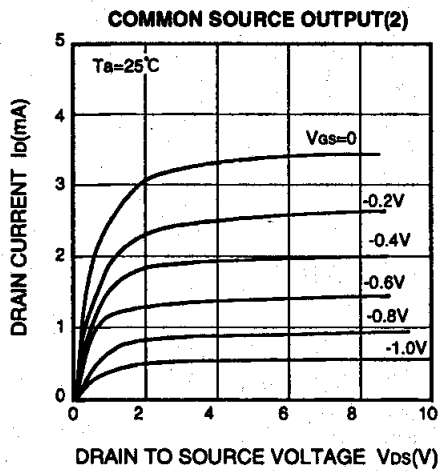
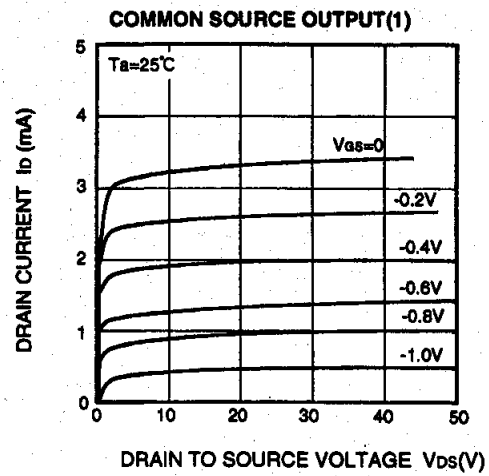
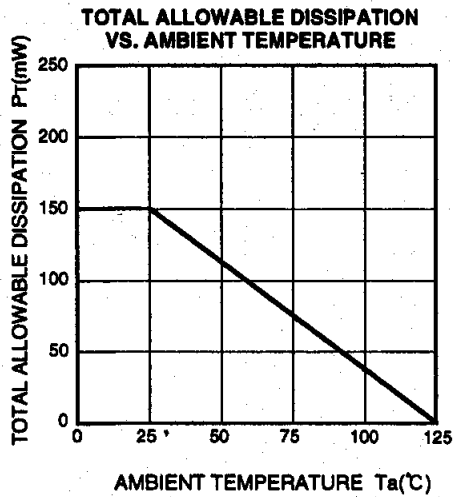
ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

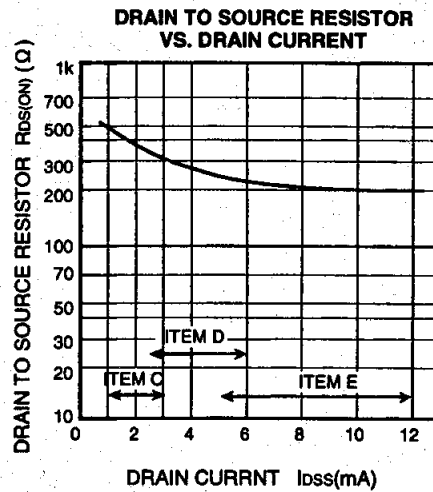
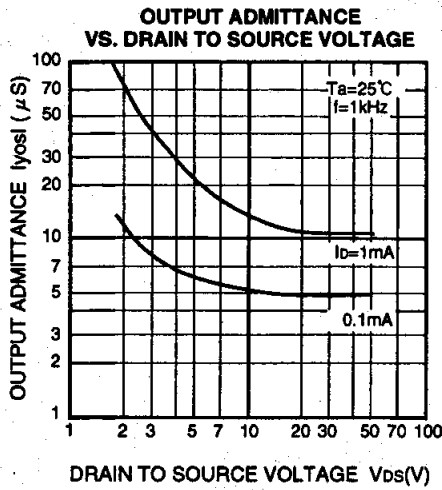
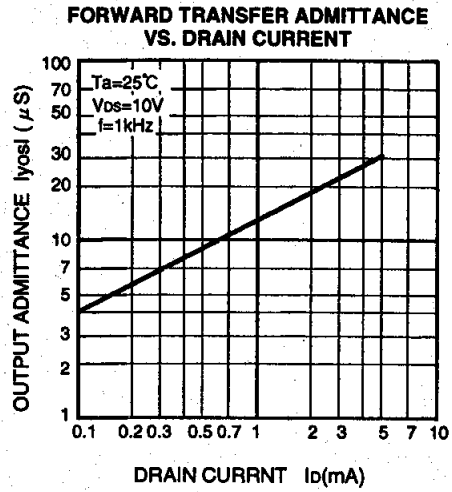
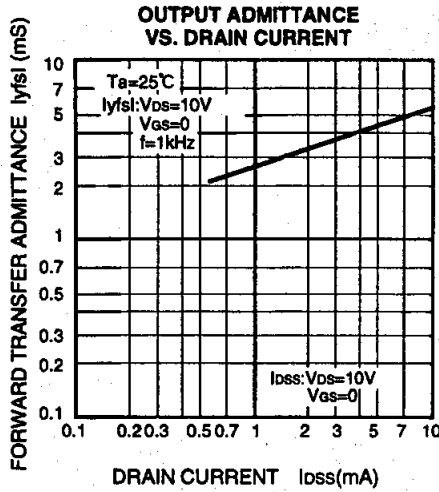
Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$V_{(BR)GDO}$	G to D break down voltage	$I_G=-10\mu\text{A}, I_S=0$	-50			V
I_{GSS}	Gate leakage current	$V_{GS}=-30\text{V}, V_{DS}=0$			-1	nA
I_{DSS}^*	Drain current	$V_{DS}=10\text{V}, V_{GS}=0$	0.6		12	mA
$V_{GS(off)}$	Cut off voltage	$V_{DS}=10\text{V}, I_D=10\mu\text{A}$	-0.3	-1.5	-6.0	V
$ y_{fs} $	Forward transfer admittance	$V_{DS}=10\text{V}, V_{GS}=0, f=1\text{kHz}$	1.0	3.0		mS
$ y_{os} $	Output admittance	$V_{DS}=10\text{V}, V_{GS}=0, f=1\text{kHz}$		10		μS
C_{iss}	Input capacitance	$V_{DS}=10\text{V}, V_{GS}=0, f=1\text{MHz}$		8		pF
C_{rss}	Feed back capacitance	$V_{DS}=10\text{V}, V_{GS}=0, f=1\text{MHz}$		1.5		pF
$R_{DS(ON)}$	Drain to source resistor	$V_{DS}=10\text{mVrms}(1\text{kHz}), V_{GS}=0, I_{DSS}=5\text{mA}$		250		Ω

* : It shows loss classification in right table.

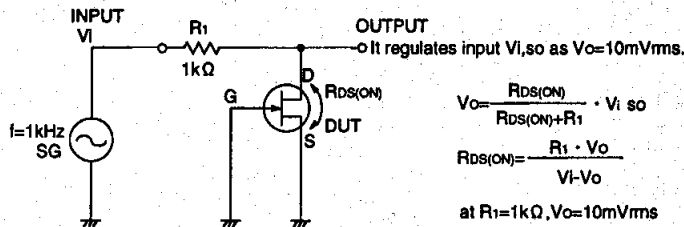
Item	B	C	D	E
loss	0.6 to 1.5	1.0 to 3.0	2.5 to 6.0	5.0 to 12

TYPICAL CHARACTERISTICS





DRAIN TO SOURCE RESISTOR $R_{ds(on)}$ TEST CIRCUIT



$$V_o = \frac{R_{ds(on)}}{R_{ds(on)} + R_1} \cdot V_i \text{ so}$$

$$R_{ds(on)} = \frac{R_1 \cdot V_o}{V_i - V_o}$$

at $R_1 = 1\text{k}\Omega$, $V_o = 10\text{mVrms}$